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**PATENT APPLICATION**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Confirmation No.: 4669

Syouji HIGASHIDA et al.

Art Unit: 2826

U.S. Application No.: 09/926,454

Examiner: Johannes P. Mondt

Filed: November 6, 2001

Attorney Dkt. No.: 107400-00044

For: SEMICONDUCTOR DEVICE

**RESPONSE UNDER 37 C.F.R. § 1.111**

Commissioner for Patents  
Washington, D.C. 20231

Date: March 24, 2003

Sir:

This paper is filed in response to the Office Action dated October 24, 2002, the time period for response having been extended from January 24, 2003 to March 24, 2003 by the enclosed Petition for Extension of Time. In the prosecution of the application identified above, please consider the following amendments.

**IN THE CLAIMS:**

Please amend claims 6 and 7 as follows:

6. (Twice Amended) The semiconductor device of claim 1, wherein a diffusion region having a different conductivity type from that of said semiconductor layer is formed on the closest side to said protective diode of said transistor cells arranged, said diffusion region having no other diffusion region therein, and said source

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